

General Description

The GreenMOS[®] high voltage MOSFET utilizes charge balance technology to achieve outstanding low on-resistance and lower gate charge. It is engineered to minimize conduction loss, provide superior switching performance and robust avalanche capability.

The GreenMOS[®] Generic series is optimized for extreme switching performance to minimize switching loss. It is tailored for high power density applications to meet the highest efficiency standards.

Features

- Low $R_{DS(on)}$ & FOM
- Extremely low switching loss
- Excellent stability and uniformity




Applications

- PC power
- LED lighting
- Telecom power
- Server power
- EV Charger
- Solar/UPS

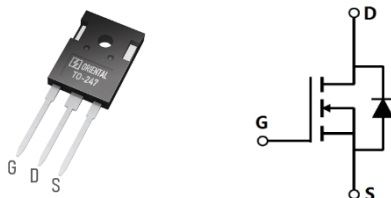
Key Performance Parameters

Parameter	Value	Unit
$V_{DS, min} @ T_{j(max)}$	700	V
$I_{D, pulse}$	120	A
$R_{DS(ON), max} @ V_{GS}=10V$	99	m Ω
Q_g	43.6	nC

Marking Information

Product Name	Package	Marking
OSG65R099HF	TO247	OSG65R099H

Package & Pin Information



Absolute Maximum Ratings at $T_j=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	650	V
Gate-source voltage	V_{GS}	± 30	V
Continuous drain current ¹⁾ , $T_C=25^\circ\text{C}$	I_D	40	A
Continuous drain current ¹⁾ , $T_C=100^\circ\text{C}$		25	
Pulsed drain current ²⁾ , $T_C=25^\circ\text{C}$	$I_{D, pulse}$	120	A
Continuous diode forward current ¹⁾ , $T_C=25^\circ\text{C}$	I_S	40	A
Diode pulsed current ²⁾ , $T_C=25^\circ\text{C}$	$I_{S, pulse}$	120	A
Power dissipation ³⁾ , $T_C=25^\circ\text{C}$	P_D	278	W
Single pulsed avalanche energy ⁵⁾	E_{AS}	1000	mJ
MOSFET dv/dt ruggedness, $V_{DS}=0\dots 480\text{ V}$	dv/dt	50	V/ns
Reverse diode dv/dt, $V_{DS}=0\dots 480\text{ V}$, $I_{SD}\leq I_D$	dv/dt	15	V/ns
Operation and storage temperature	T_{stg}, T_j	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	$R_{\theta JC}$	0.45	$^\circ\text{C/W}$
Thermal resistance, junction-ambient ⁴⁾	$R_{\theta JA}$	62	$^\circ\text{C/W}$

Electrical Characteristics at $T_j=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	650			V	$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$
		700	770			$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$, $T_j=150^\circ\text{C}$
Gate threshold voltage	$V_{GS(th)}$	3.0		4.0	V	$V_{DS}=V_{GS}$, $I_D=1\text{ mA}$
Drain-source on-state resistance	$R_{DS(on)}$		0.08	0.099	Ω	$V_{GS}=10\text{ V}$, $I_D=20\text{ A}$
			0.205			$V_{GS}=10\text{ V}$, $I_D=20\text{ A}$, $T_j=150^\circ\text{C}$
Gate-source leakage current	I_{GSS}			100	nA	$V_{GS}=30\text{ V}$
				-100		$V_{GS}=-30\text{ V}$
Drain-source leakage current	I_{DSS}			1	μA	$V_{DS}=650\text{ V}$, $V_{GS}=0\text{ V}$

Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{iss}		3042.6		pF	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, $f=200\text{ kHz}$
Output capacitance	C_{oss}		200.6		pF	
Reverse transfer capacitance	C_{rss}		3.9		pF	
Turn-on delay time	$t_{d(on)}$		68.1		ns	$V_{GS}=10\text{ V}$, $V_{DS}=400\text{ V}$, $R_G=25\ \Omega$, $I_D=20\text{ A}$
Rise time	t_r		53.7		ns	
Turn-off delay time	$t_{d(off)}$		109.6		ns	
Fall time	t_f		56.4		ns	

Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q_g		43.6		nC	$V_{GS}=10\text{ V}$, $V_{DS}=400\text{ V}$, $I_D=20\text{ A}$
Gate-source charge	Q_{gs}		13		nC	
Gate-drain charge	Q_{gd}		13.4		nC	
Gate plateau voltage	$V_{plateau}$		5.6		V	

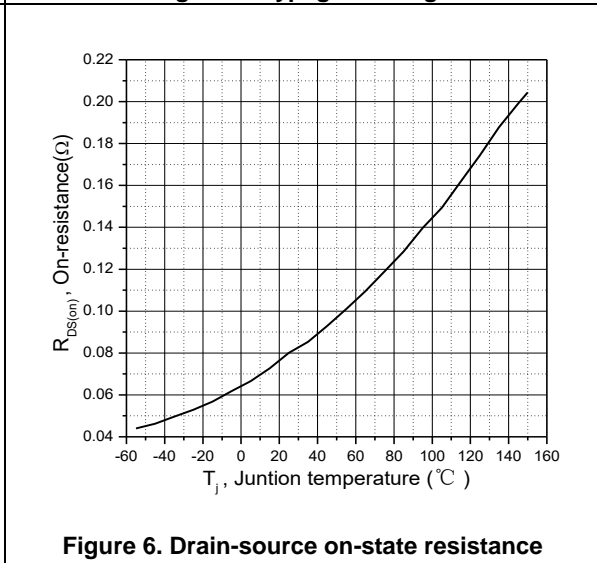
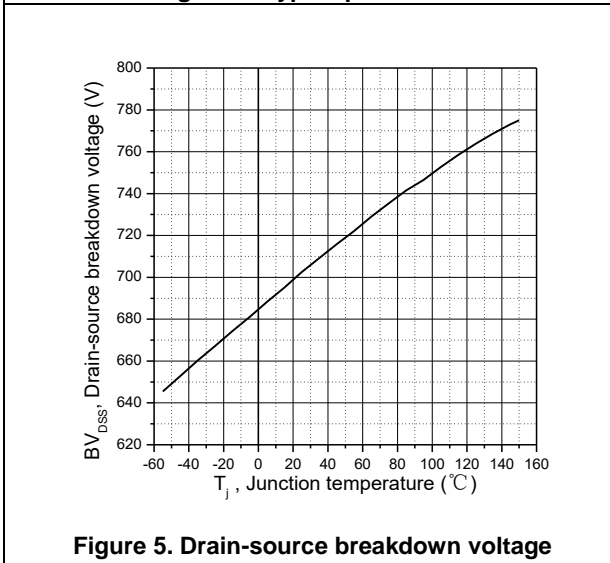
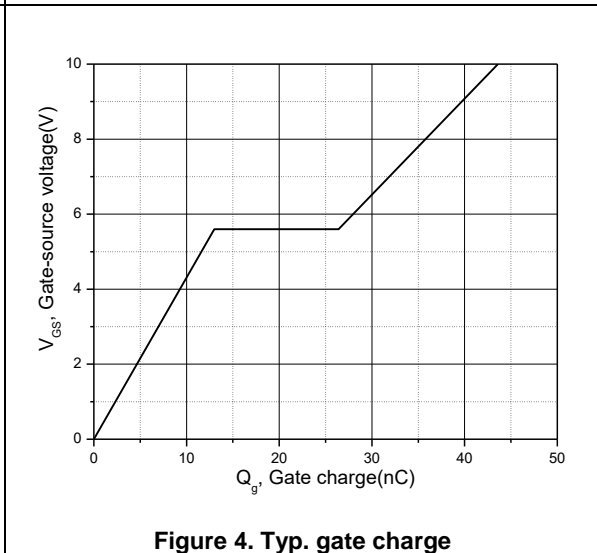
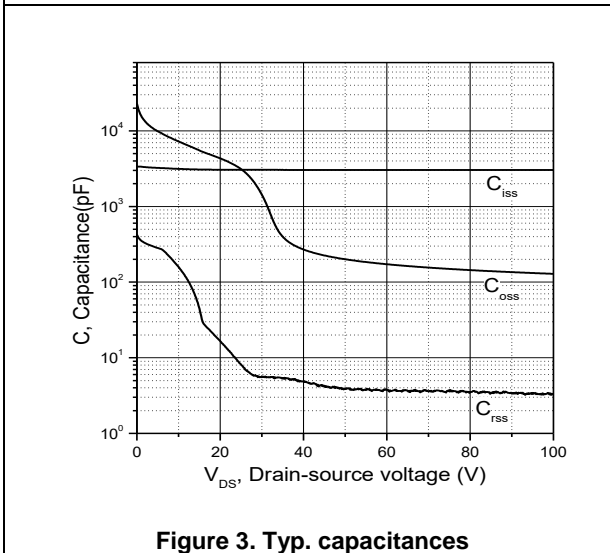
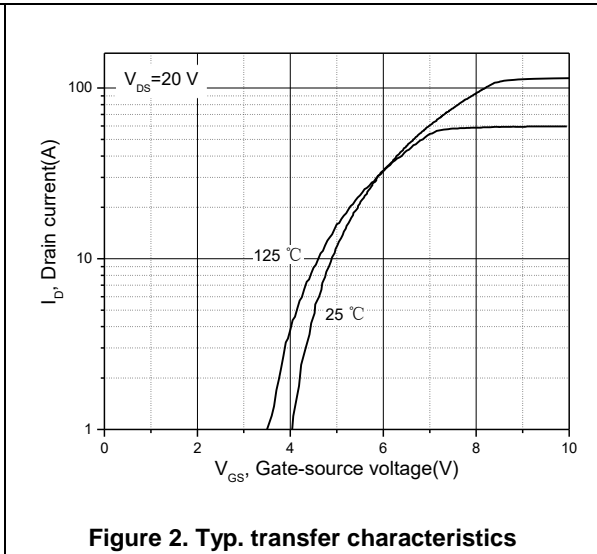
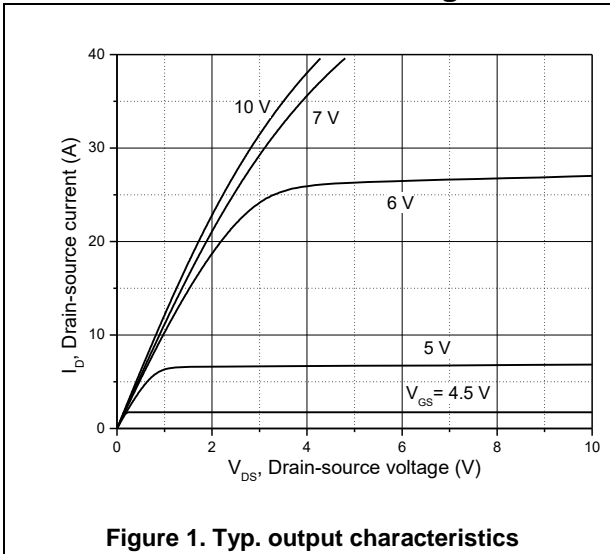
Body Diode Characteristics

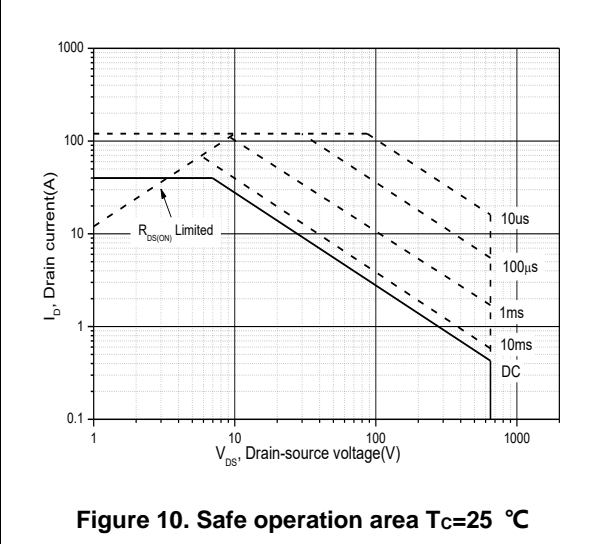
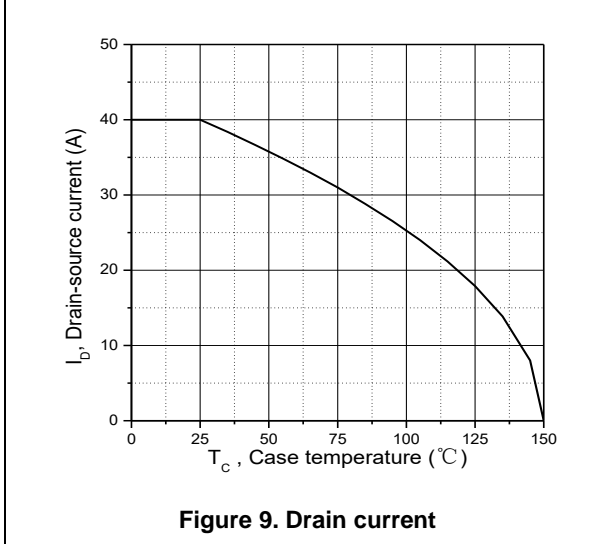
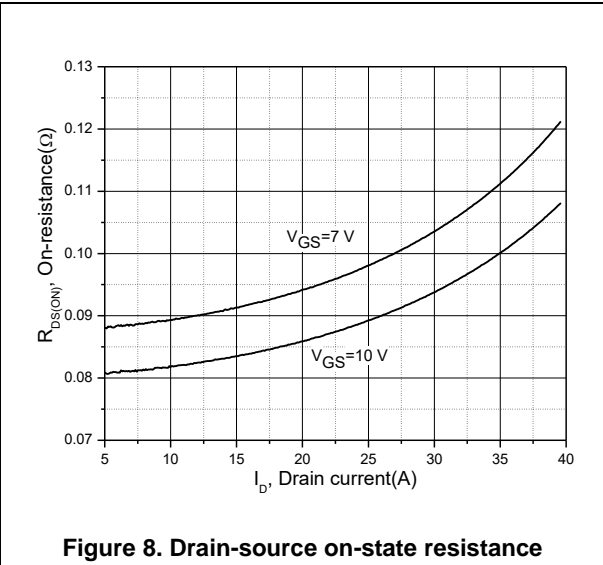
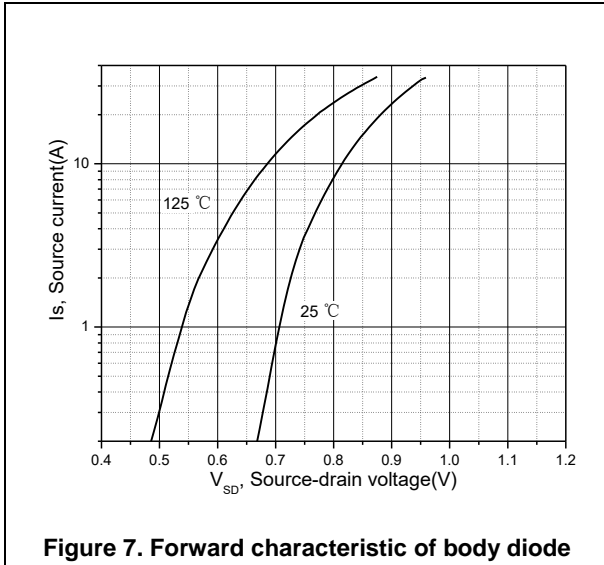
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward voltage	V_{SD}			1.4	V	$I_S=40\text{ A}$, $V_{GS}=0\text{ V}$
Reverse recovery time	t_{rr}		441.5		ns	$I_S=20\text{ A}$, $di/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	Q_{rr}		7.5		μC	
Peak reverse recovery current	I_{rrm}		31.2		A	

Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3) P_d is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_a=25\text{ }^\circ\text{C}$.
- 5) $V_{DD}=100\text{ V}$, $V_{GS}=10\text{ V}$, $L=20\text{ mH}$, starting $T_j=25\text{ }^\circ\text{C}$.

Electrical Characteristics Diagrams





Test circuits and waveforms

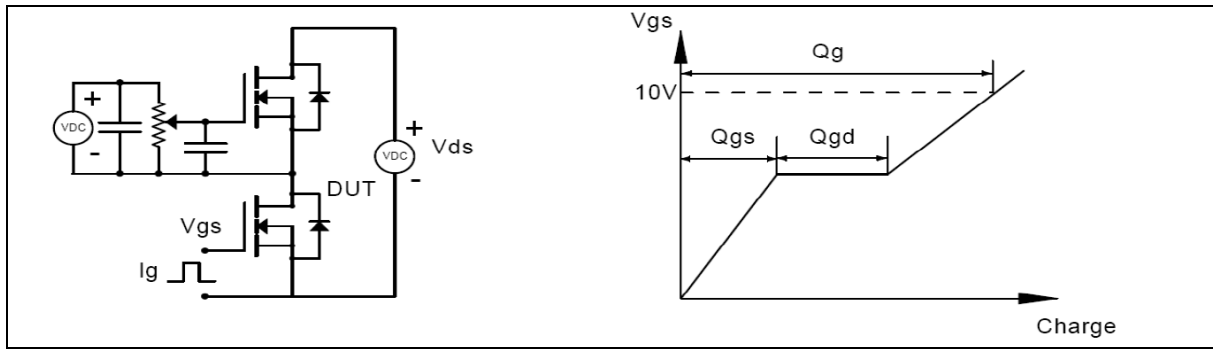


Figure 1. Gate charge test circuit & waveform

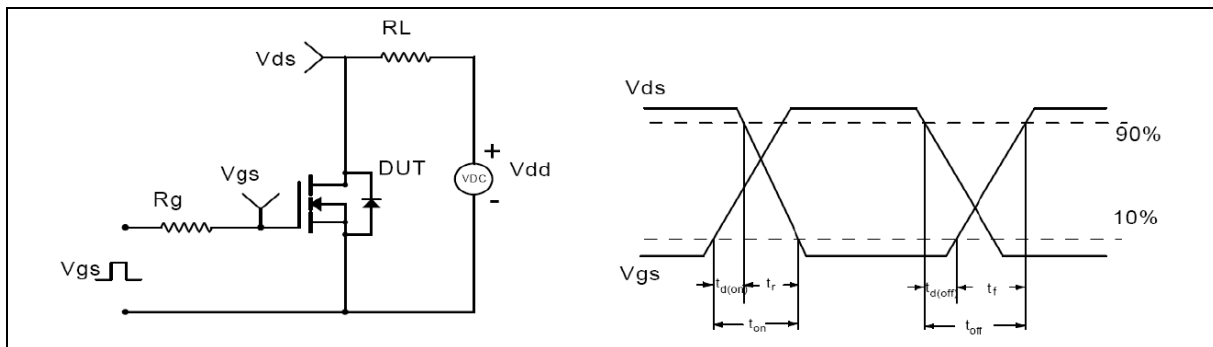


Figure 2. Switching time test circuit & waveforms

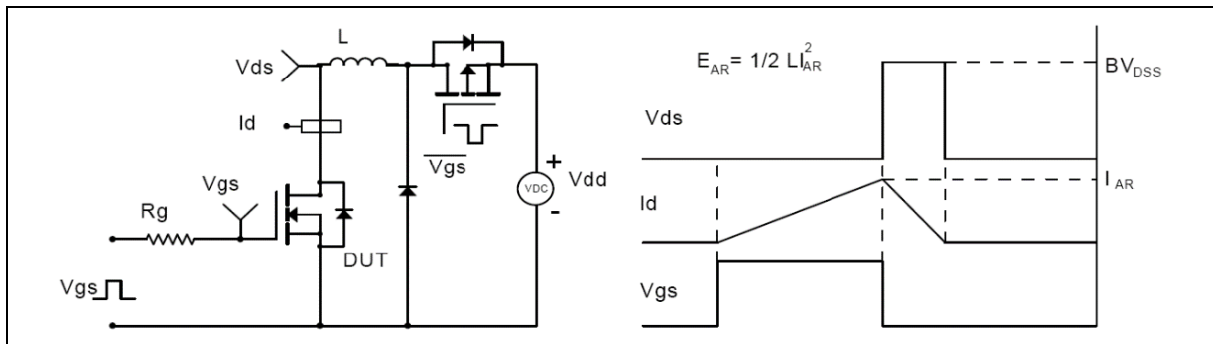


Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms

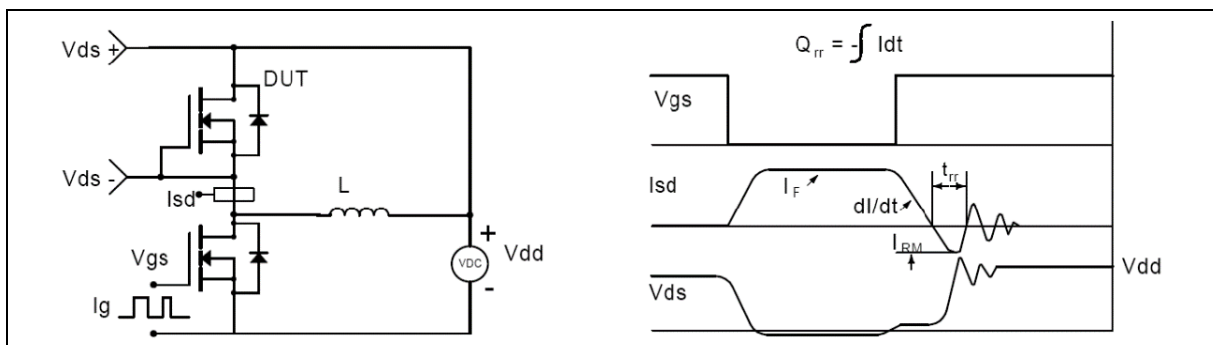


Figure 4. Diode reverse recovery test circuit & waveforms

Ordering Information

Package Type	Units/ Tube	Tubes/ Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
TO247-C	30	11	330	6	1980

Product Information

Product	Package	Pb Free	RoHS	Halogen Free
OSG65R099HF	TO247	yes	yes	yes

Legal Disclaimer

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